

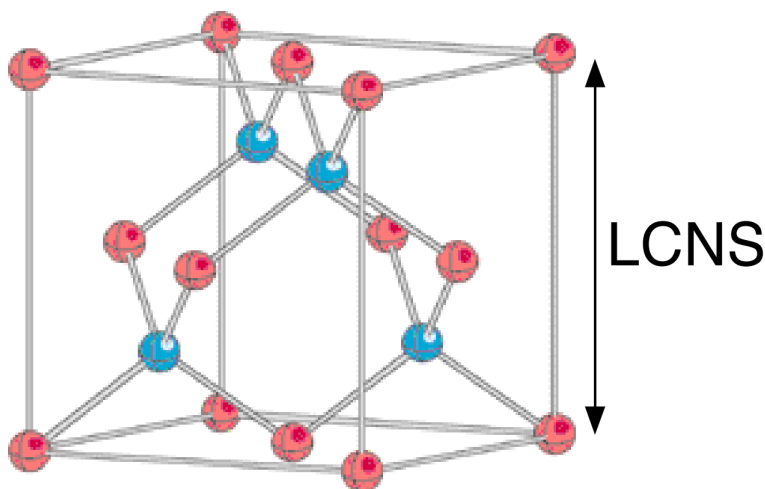
PHYS516 ASSIGNMENT 6

TIGHT BINDING MODEL OF ELECTRONIC STRUCTURES

Due: Friday, March 26, 2021

In this assignment, you will calculate the electronic structure of a small crystal of silicon atoms, based on the tight binding model explained in the lecture.

To set up atomic coordinates in a Si crystal, use the function `InitConf()` in the program `tb_util_angstrom.c` or `tb_util_au.c` at the class homepage (either use angstrom or atomic unit of your choice to specify length). This function reads the numbers of crystalline unit cells, `InitUcell[0]`, `InitUcell[1]` and `InitUcell[2]`, to be repeated in the x, y and z directions, respectively. Since the cubic unit cell of Si crystal (which takes the diamond structure, see the figure below) contains 8 atoms, your crystal will consist of $n_{\text{Atom}} = 8 \times \text{InitUcell}[0] \times \text{InitUcell}[1] \times \text{InitUcell}[2]$ atoms. In the bulk Si crystal, the lattice constant (the edge length of the cubic unit cell) is $LCNS = 5.43 \text{ \AA} = 10.2622 \text{ atomic unit}$.



The following lists relevant data structures.

```
int nAtom;           /* # of atoms */
double r[NMAX][3];   /* r[i][0|1|2] is the x|y|z coordinate of atom i */
```

where NMAX is the maximum number of atoms that can be handled with this program.

1. Write a program that sets up a $4n_{\text{Atom}} \times 4n_{\text{Atom}}$ Hamiltonian matrix (using the s-p basis set explained in the lecture, 4 orbitals/atom $\times n_{\text{Atom}}$ atoms) and diagonalizes it to obtain $4n_{\text{Atom}}$ eigenenergies. (Use the periodic boundary condition, as implemented in the molecular dynamics program, `md.c`, to mimic a bulk crystal.)

To use matrix diagonalization functions in *Numerical Recipes* (given in `eigen.c` at the class homepage), you need to define a matrix and vector as follows:

```
double **h;          /* Hamiltonian matrix */
double *d;           /* Eigenvalues */
double *e;           /* Work array for matrix diagonalization */
```

Then the following code section uses the *Numerical Recipes* utility functions, `dmatrix` and `dvector`, to allocate memory to use matrix, `h[i][j]`, in the range $1 \leq i \leq n_4$ and $1 \leq j \leq n_4$,

and vectors, $d[i]$ and $e[i]$, in the range $1 \leq i \leq n4$, where $n4 = 4 \times n_{\text{Atom}}$ is the size of the basis set.

```
n4 = 4*nAtom;
h = dmatrix(1,n4,1,n4);
d = dvector(1,n4);
e = dvector(1,n4);
```

After setting up the $n4 \times n4$ Hamiltonian matrix, you will diagonalize it with the *Numerical Recipes* functions, `tred2` (which reduces the symmetric Hamiltonian matrix into a tridiagonal form) and `tqli` (which diagonalizes the tridiagonal matrix).

```
tred2(h,n4,d,e);
tqli(d,e,n4,h);
```

2. Choose `InitUcell[0] = InitUcell[1] = InitUcell[2] = 1` and diagonalize the resulting 32×32 Hamiltonian matrix for three different values of lattice constant: $LCNS = 1.8 \times 5.43 \text{ \AA}$, $1.4 \times 5.43 \text{ \AA}$, and $1 \times 5.43 \text{ \AA}$. For each lattice constant, plot the density of states defined as follows:

$$D(\varepsilon) = \sum_{v=1}^{n4} \frac{1}{\sqrt{\pi}\sigma} \exp\left(-\frac{(\varepsilon - \varepsilon_v)^2}{\sigma^2}\right)$$

where $\sigma = 0.1 \text{ eV} = 0.003675 \text{ au}$ is the energy spread given to each energy eigenvalue, ε_v , to obtain a smooth density-of-states curve. Plot $D(\varepsilon)$ vs. ε and discuss the effect of lattice constant on the density of states.

3. Choose `InitUcell[0] = InitUcell[1] = InitUcell[2] = 2` ($n_{\text{Atom}} = 8 \times 2^3 = 64$), diagonalize the resulting 256×256 Hamiltonian matrix for $LCNS = 5.43 \text{ \AA}$, and plot the density-of-states $D(\varepsilon)$ vs. ε . How does this density of states differ from the one with the same lattice constant calculated above for 8 atoms?
4. Consider the eigenenergies for 64 atoms and the bulk Si lattice constant, $LCNS = 5.43 \text{ \AA}$. Determine the Fermi distribution,

$$f(\varepsilon_v) = \frac{2}{\exp((\varepsilon_v - \mu)/k_B T) + 1},$$

for all the 256 eigenenergies, where $T = 0.2 \text{ eV}/k_B$ (k_B is the Boltzmann constant) = $0.2 \times 11604.5 \text{ K} = 2320.9 \text{ K}$ is the temperature and μ is the chemical potential to satisfy

$$\sum_v f(\varepsilon_v) = 4N = 256.$$

(Note that there are 4 valence electrons from each of the 64 Si atoms). Plot $f(\varepsilon_v)$ vs. ε_v .

Submit your code (#1 above) and all plots (three plots for #2, one plot for #3, and one for #4).